

Silicon NPN Power Transistors

2N3234

DESCRIPTION

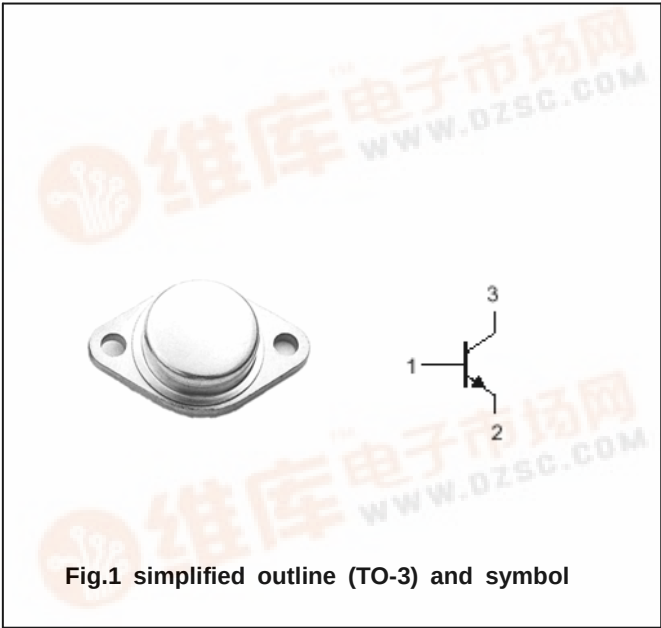
- With TO-3 package
- Excellent safe operating area
- Low collector saturation voltage

APPLICATIONS

- For audio amplifier and power switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	160	V
V _{CEO}	Collector-emitter voltage	Open base	160	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		7.5	A
P _C	Collector power dissipation	T _C =25℃	115	W
T _j	Junction temperature		150	℃
T _{stg}	Storage temperature		-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{(th) jc}	Thermal resistance junction to case	1.17	℃/W



Silicon NPN Power Transistors

2N3234

CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=30mA ; I_B=0$	160			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C=5A ; I_B=0.5A$			1.0	V
$V_{BE(on)}$	Base-emitter on voltage	$I_C=3A ; V_{CE}=4V$			1.5	V
I_{CEO}	Collector cut-off current	$V_{CE}=80V ; I_B=0$			0.7	mA
I_{CBO}	Collector cut-off current	$V_{CB}=160V ; I_E=0$			0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=7V ; I_C=0$			0.1	mA
h_{FE}	DC current gain	$I_C=5A ; V_{CE}=10V$	18		55	

Silicon NPN Power Transistors

2N3234

PACKAGE OUTLINE

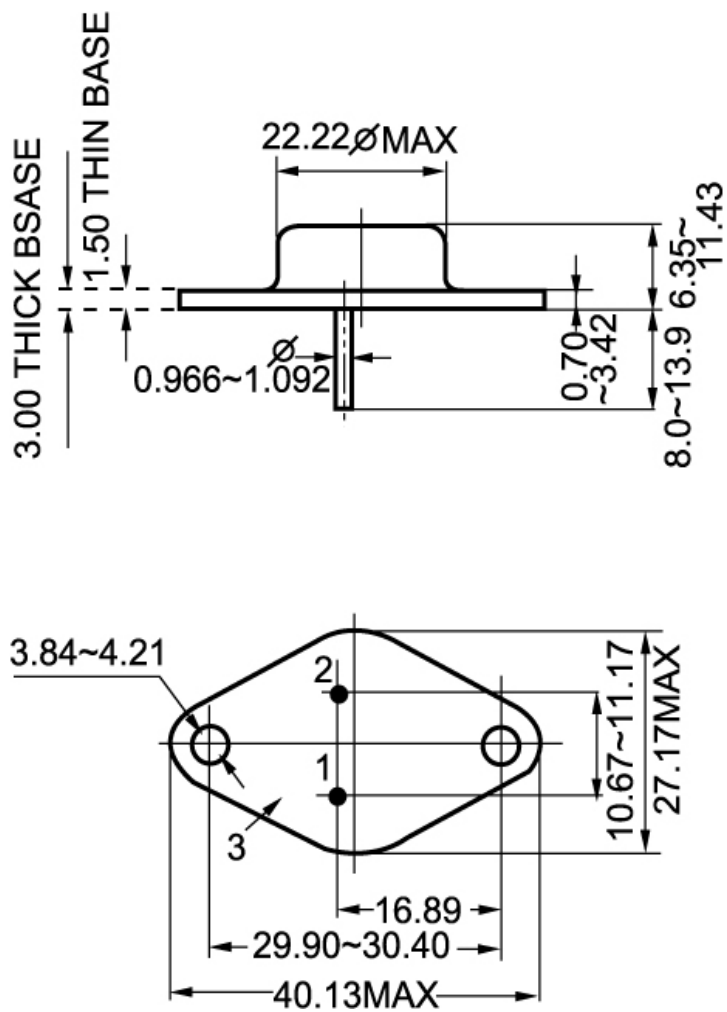


Fig.2 outline dimensions (unindicated tolerance: $\pm 0.1\text{mm}$)